

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L11	1494	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor))) and @ad<"20030121" and ((gate near5 (oxide or insulat\$4 or dielectric)) with (boron or boride))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 01:40
L12	301	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor))) and @ad<"20030121" and (((gate near5 (oxide or insulat\$4 or dielectric)) with (boron or boride or arsenic)) same (p?mos or p?mosfet or p?fet or pmos or pmosfet or pfet))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 01:45
L13	67	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor))) and @ad<"20030121" and (((gate near5 (oxide or insulat\$4 or dielectric)) with (arsenic or arsenide)) same (p?mos or p?mosfet or p?fet or pmos or pmosfet or pfet))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 01:52
L14	301	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor))) and @ad<"20030121" and (((gate near5 (oxide or insulat\$4 or dielectric)) with (boron or boride or b)) same (n?mos or n?mosfet or n?fet or nmos or nmosfet or nfet))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 01:53

## EAST Search History

L15	170	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor))) and @ad<"20030121" and (((gate near5 (oxide or insulat\$4 or dielectric)) with (boron or boride)) same (n?mos or n?mosfet or n?fet or nmos or nmosfet or nfet))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 01:53
L16	131	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$5 or dielectric)) same (halfnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:01
L17	210	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$5 or dielectric)) same (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or iii or iv or v))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:04
L18	132	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$5 or dielectric)) same (halfnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:06

## EAST Search History

L19	258	257/369.ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf or yttrium or Y or lutetium or lu or lawrencium or lr or aluminum or al)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:07
L20	104	257/369.ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:08
L21	289	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf or yttrium or Y or lutetium or lu or lawrencium or lr or aluminum or al)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:13
L22	290	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or aluminum or al)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:18

## EAST Search History

L23	290	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 02:23
L24	45	(257/645 or 257/651).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$5 or dielectric) with (arsenic or as or boron or B or aluminum or al or gallium or ga or indium or in or thallium or tl or ("3" or "iii") near3 (element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 02:25
L26	2404	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" or "4") near3 (metal or element or compound)))) same (arsenic or as or boron or b or gallium or ga or indium or thallium or tl)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 02:28

## EAST Search History

L27	752	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" or "4") near3 (metal or element or compound)))) same (arsenic or boron or gallium or ga or indium or thallium or tl)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/21 02:29
L28	195	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or b))) and (((positive or negative) near4 charg\$4) with (dop\$4 or insulat\$4 or dielectric or oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:30
L29	619	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or b or arsenic or as))) and (((positive or negative) near4 charg\$4) with (dop\$4 or insulat\$4 or dielectric or oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:31

## EAST Search History

L30	210	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or b or arsenic))) and (((positive or negative) near4 charg\$4) with (dop\$4 or insulat\$4 or dielectric or oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/21 02:32
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